

Device Modeling Report

COMPONENTS:

DIODE/ SCHOTTKY RECTIFIER/ PROFESSIONAL

PART NUMBER: 1SS349

MANUFACTURER: TOSHIBA



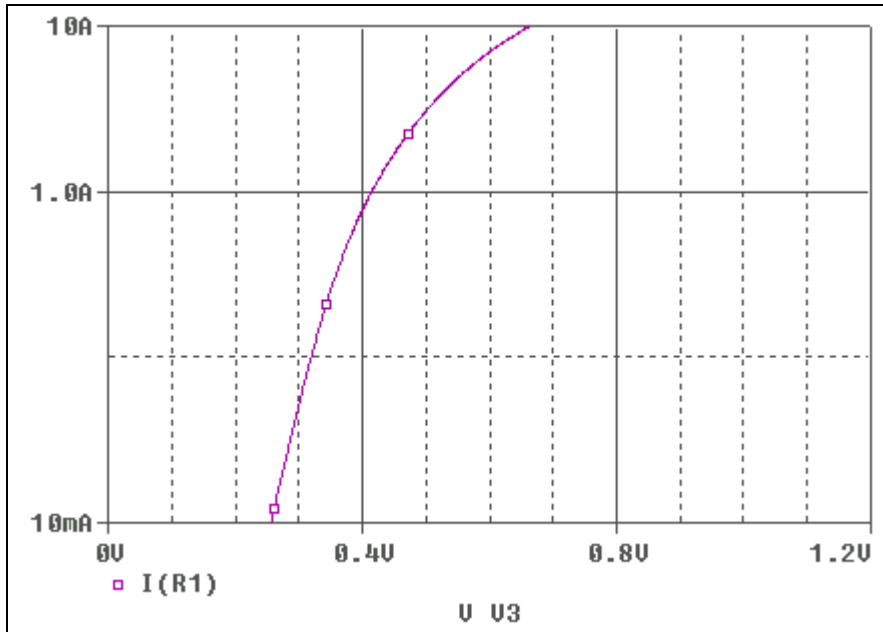
Bee Technologies Inc.

DIODE SPICE MODEL

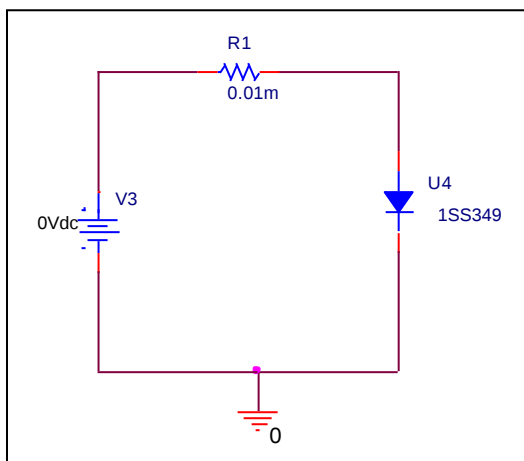
PSpice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time
EG	Energy-band Gap

Forward Current Characteristic

Circuit Simulation Result

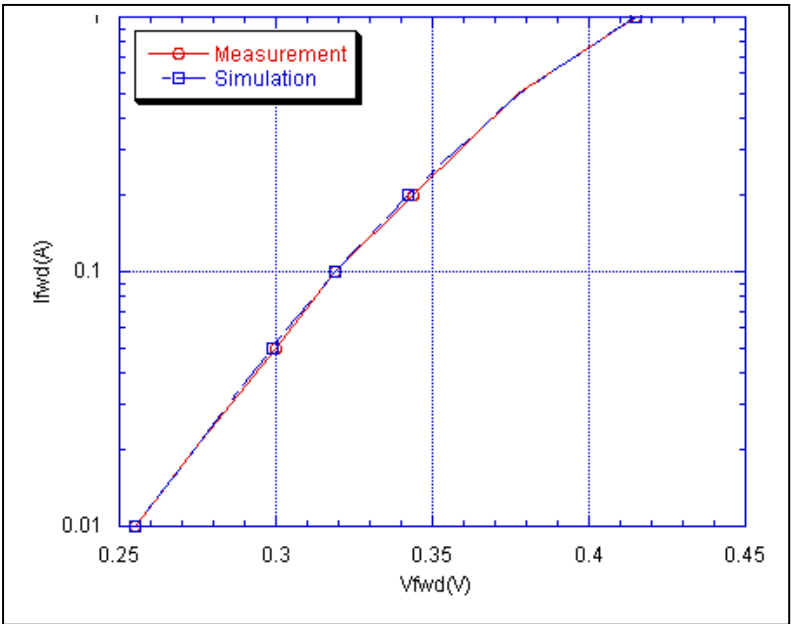


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

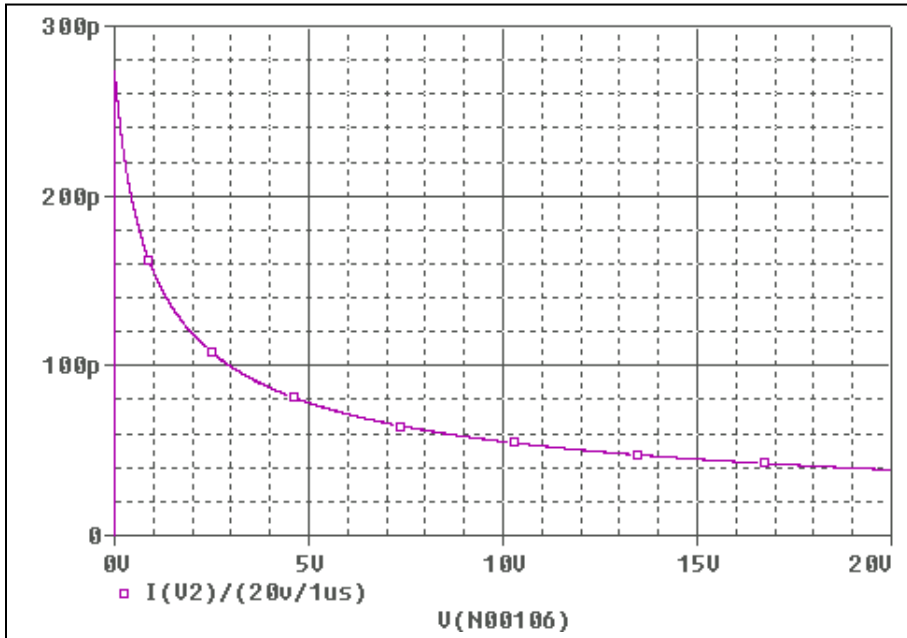


Simulation Result

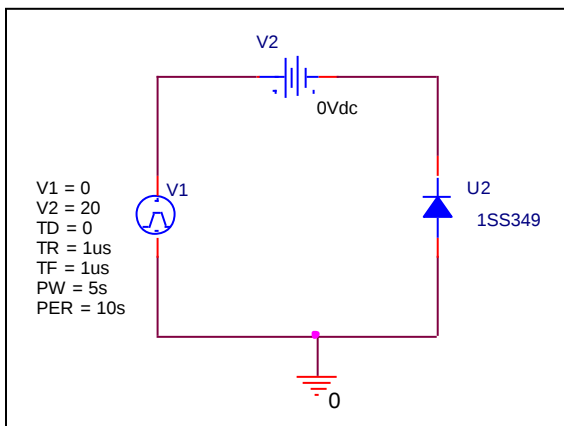
Ifwd(A)	Vfwd(V) Measurement	Vfwd(V) Simulation	%Error
0.01	0.257	0.255	-0.78
0.02	0.275	0.274	-0.36
0.05	0.300	0.299	-0.33
0.1	0.320	0.319	-0.31
0.2	0.344	0.342	-0.58
0.5	0.377	0.378	0.27
1	0.416	0.415	-0.24

Junction Capacitance Characteristic

Circuit Simulation Result

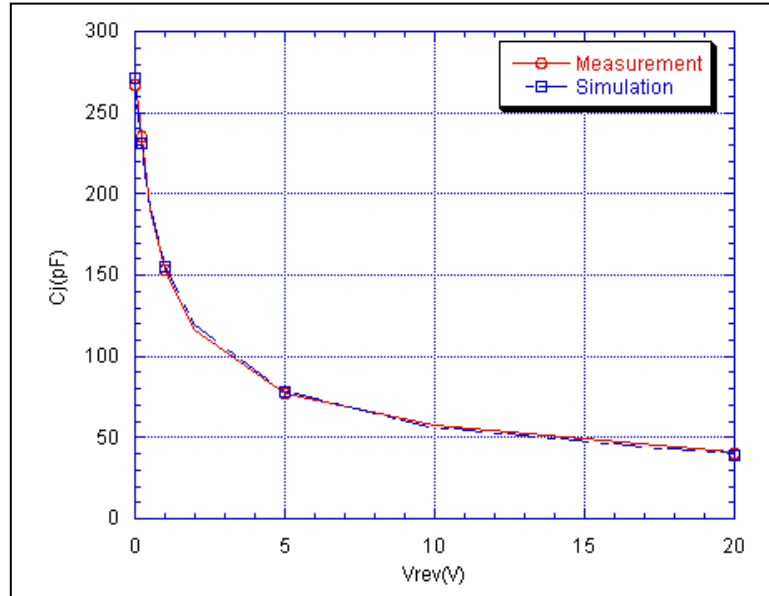


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

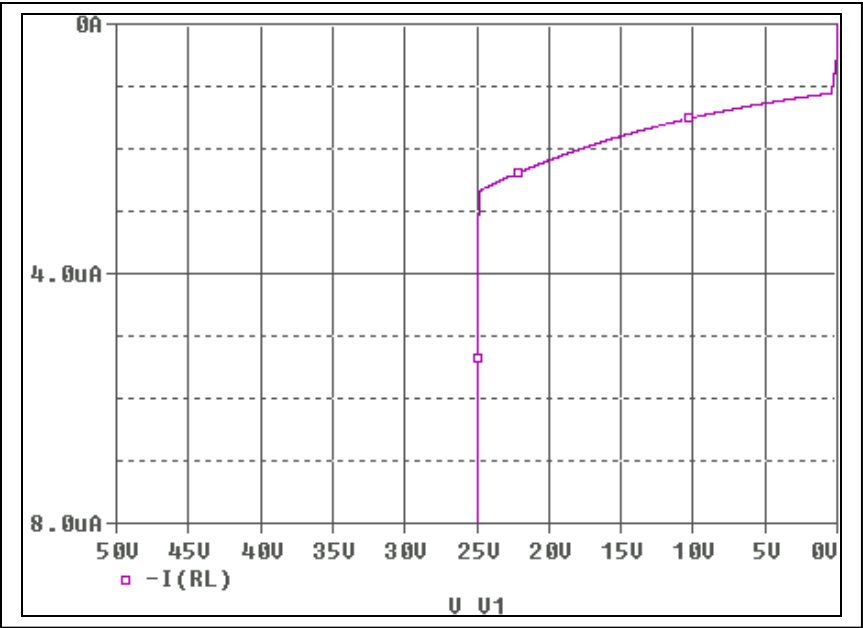


Simulation Result

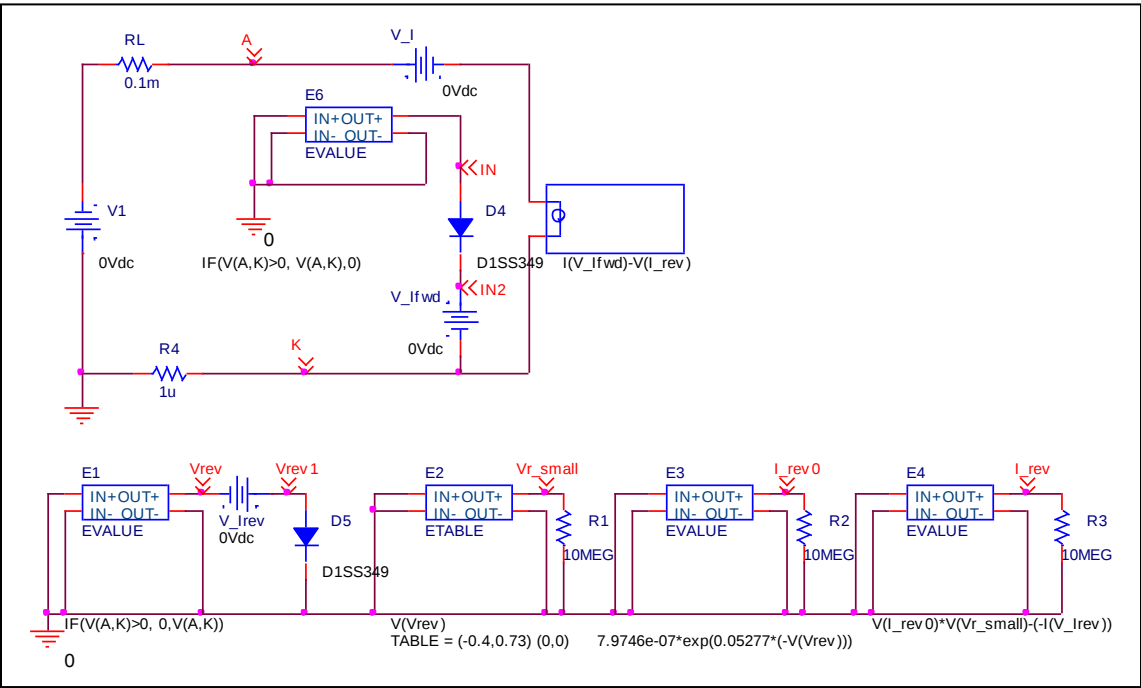
V_{rev} (V)	C_j (pF) Measurement	C_j (pF) Simulation	%Error
0	267.605	271.600	1.49
0.1	254.373	249.593	-1.88
0.2	235.613	230.580	-2.14
0.5	190.842	192.148	0.68
1	152.713	154.828	1.38
2	115.885	118.750	2.47
5	77.354	78.011	0.85
10	57.421	55.277	-3.73
20	40.519	38.720	-4.44

Reverse Characteristic

Circuit Simulation Result

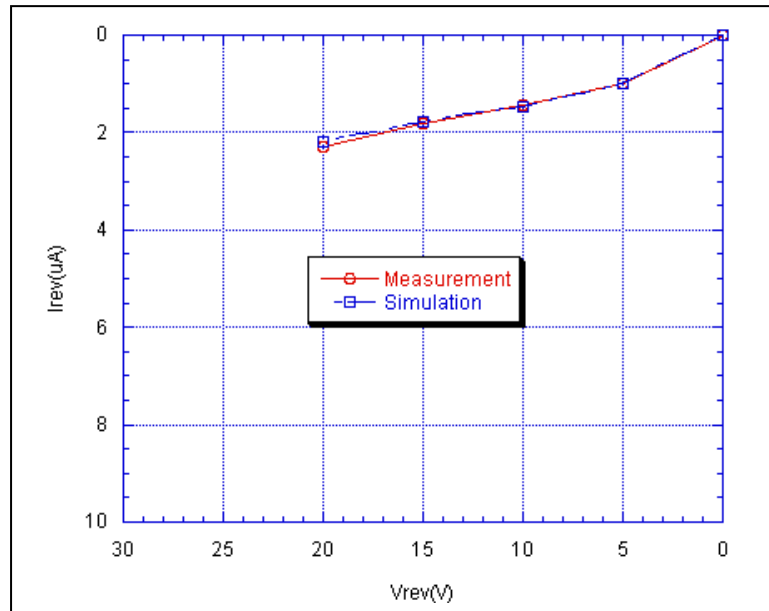


Evaluation Circuit



Comparison Graph

Circuit Simulation Result



Simulation Result

$V_{rev}(V)$	$I_{rev}(\mu A)$ Measurement	$I_{rev}(\mu A)$ Simulation	%Error
20	2.300	2.200	-4.35
15	1.800	1.790	-0.56
10	1.450	1.490	2.76

Reverse Characteristic

Reference

